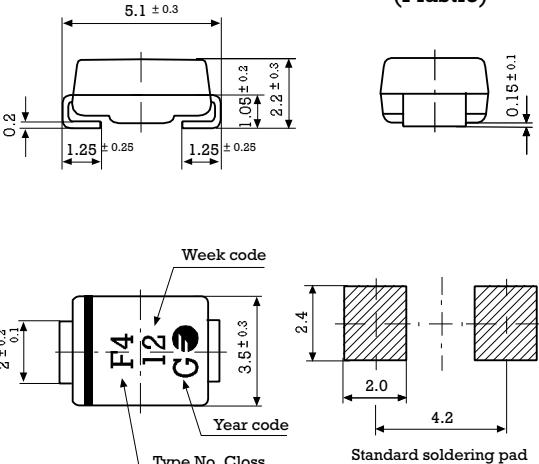


## 2 Amp. Surface Mounted Schottky Barrier Rectifier

Dimensions in mm.	CASE: SMB/DO-214AA (Plastic)	Voltage 20 V to 60 V	Current 2.0 A
 <ul style="list-style-type: none"> <li>• Metal Silicon Junction, majority carrier conduction</li> <li>• High current capability, low forward voltage drop</li> <li>• Guardring for overvoltage protection</li> <li>• Low power loss, high efficiency</li> <li>• High surge capability</li> <li>• Plastic material carries U/L recognition 94VO</li> <li>• Low profile package</li> <li>• Easy pick and place</li> </ul>			

### Maximum Ratings, according to IEC publication No. 134

		FSS22	FSS23	FSS24	FSS25	FSS26
	Marking Code	B1	B2	B3	B4	B5
$V_{RRM}$	Peak recurrent reverse voltage (V)	20	30	40	50	60
$V_{RMS}$	Maximum RMS voltage (V)	14	21	28	35	42
$V_{DC}$	Maximum DC blocking voltage (V)	20	30	40	50	60
$I_F(AV)$	Maximum average Forward current.	2 A				
$I_{FSM}$	8.3 ms. peak forward surge current (Jedec Method)	50 A				
$T_j$	Operating temperature range	– 65 to + 125 °C		– 65 to + 150 °C		
$T_{stg}$	Storage temperature range	– 65 to + 150 °C				

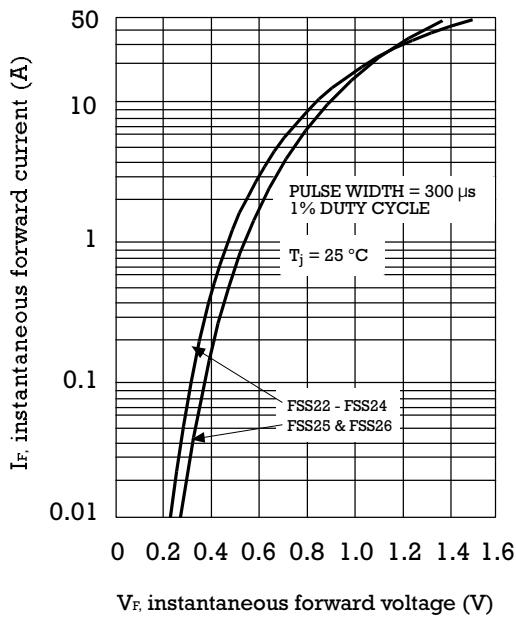
### Electrical Characteristics at Tamb = 25 °C

$V_F$	Max. forward voltage drop at $I_F = 2.0 \text{ A}^{(1)}$	0.55 V	0.70 V
$I_R$	Max. Instantaneous reverse current at $V_{RRM}$ <sup>(1)</sup>	0.5 mA	
		20 mA	10 mA
$R_{thj-a}$ $R_{thj-l}$		75 °C/W 17 °C/W	

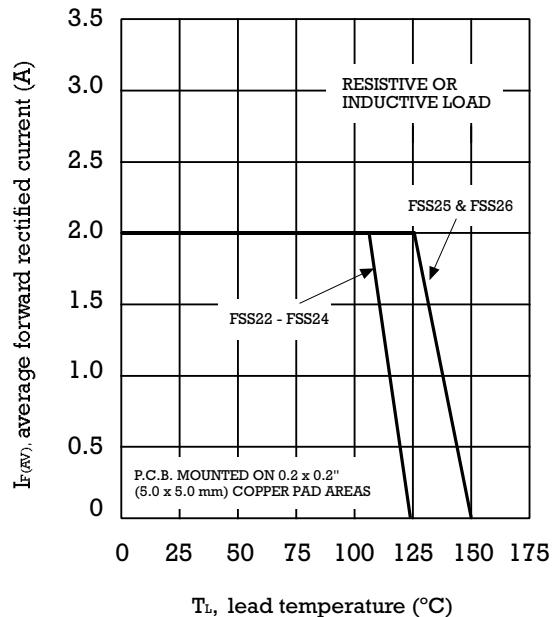
NOTE: Thermal Resistance from junction to lead or to ambient PCB mounted with 5x5 mm copper pads areas.

(1) Pulse test: 300µs pulse width, 1% duty cycle.

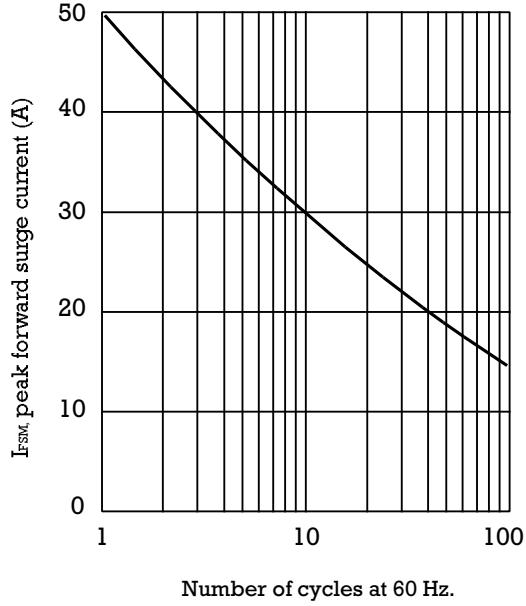
TYPICAL FORWARD CHARACTERISTIC



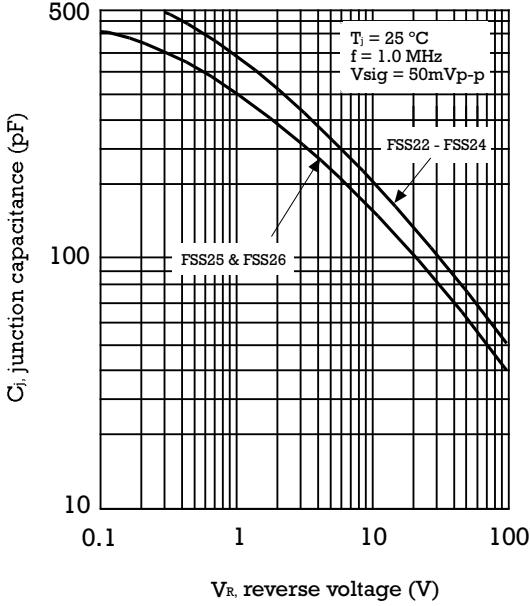
FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

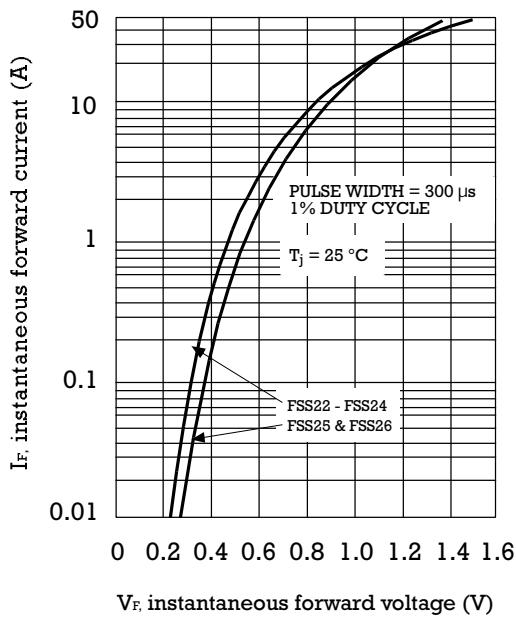


TYPICAL JUNCTION CAPACITANCE

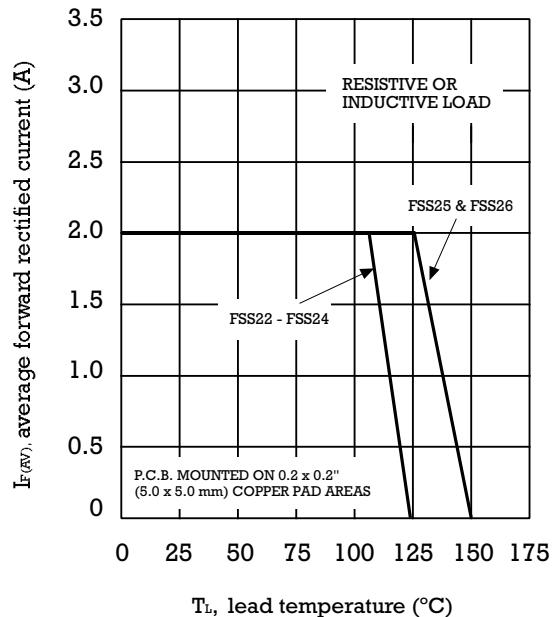


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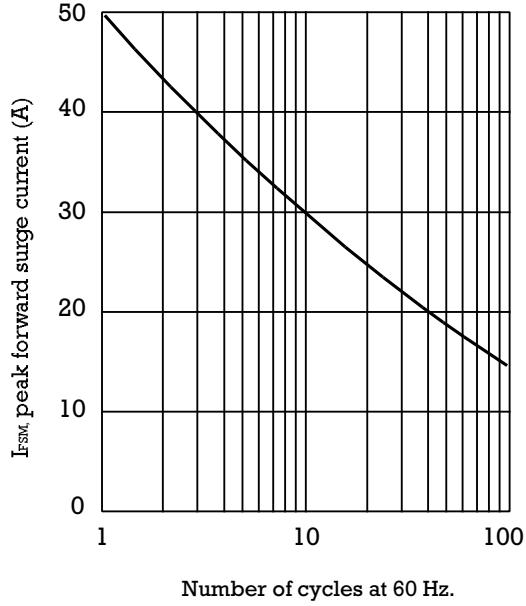
TYPICAL FORWARD CHARACTERISTIC



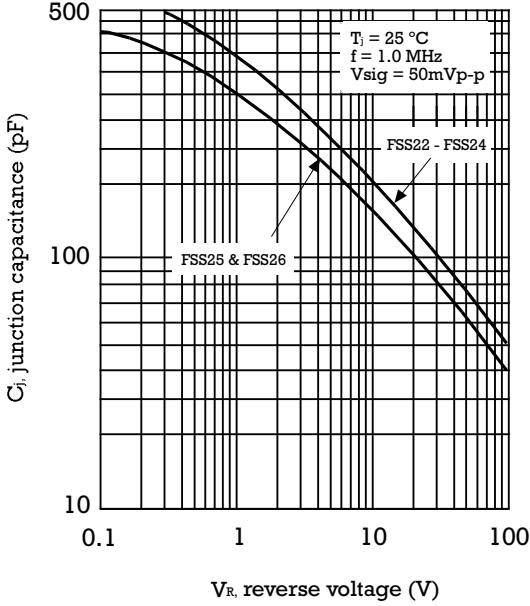
FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



TYPICAL JUNCTION CAPACITANCE



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